















## Bill of Materials

Designator	Description	Value	Q
C1	Electrolytic capacitor 16v/50v	10µF	1
C2, C3, C4, C5, C6,	Ceramic capacitor	100nF	8
IC1, IC2, IC4	4-Bits 2-Line to 1 Line data selector	74LS157	3
IC3	Non inverting bus transceiver	74LS245	1
IC5	Quad 2-input NAND gates	74LS00	1
IC6	Hex inverters	74LS04	1
MEM1, MEM2	SRAM 16x1 inverted outputs	74LS189	2
P1	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 16	16p	1
P2	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 32	р	1
P4	Socket Header, THT, pitch 2.54mm, Dual Row, Vertical,	24p	1
P5	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 8p	8p	1
R1, R2	Resistor Axial	4.7K	2
RN1	Resistor array 8 elements,9 pins	330Ω	1
SW1	DIP switch 8 positions	8 pos	1
SW2	Mini slide switch 2 pos, 3 pins		1
SW3	Tactile button 6 mm	6mm	1



## Assembly List

Designator	Description	Value
C1	Electrolytic capacitor 16v/50v	10µF
C2	Ceramic capacitor	100nF
C3	Ceramic capacitor	100nF
C4	Ceramic capacitor	100nF
C5	Ceramic capacitor	100nF
C6	Ceramic capacitor	100nF
C7	Ceramic capacitor	100nF
C8	Ceramic capacitor	100nF
C9	Ceramic capacitor	100nF
IC1	4-Bits 2-Line to 1 Line data selector	74LS157
IC2	4-Bits 2-Line to 1 Line data selector	74LS157
IC3	Non inverting bus transceiver	74LS245
IC4	4-Bits 2-Line to 1 Line data selector	74LS157
IC5	Quad 2-input NAND gates	74LS00
IC6	Hex inverters	74LS04
MEM1	SRAM 16x1 inverted outputs	74LS189
MEM2	SRAM 16x1 inverted outputs	74LS189
P1	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 16p	16p
P2	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 32p	
P4	Socket Header, THT, pitch 2.54mm, Dual Row, Vertical, 24r	24p
P5	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 8p	8p
R1	Resistor Axial	4.7K
R2	Resistor Axial	4.7K
RN1	Resistor array 8 elements,9 pins	330Ω
SW1	DIP switch 8 positions	8 pos
SW2	Mini slide switch 2 pos, 3 pins	
SW3	Tactile button 6 mm	6mm